



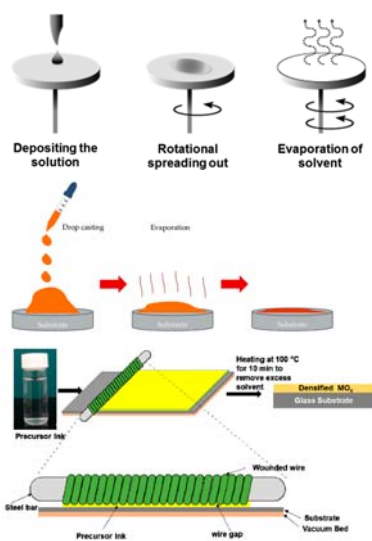
Paracyclophane derivatives and thin film coating via CVD process

Department of Chemical Engineering and Applied Chemistry
Chungnam National University

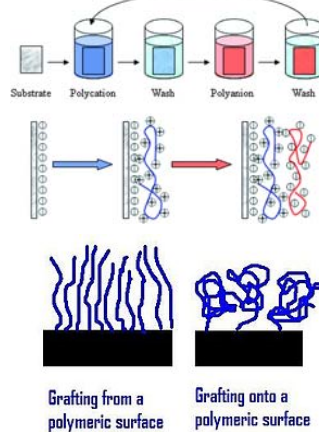
Polymeric films onto surfaces



Conventional methods



Other methods (?)



I. Vapor Deposition Polymerization

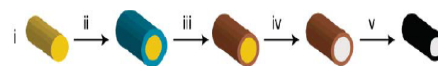
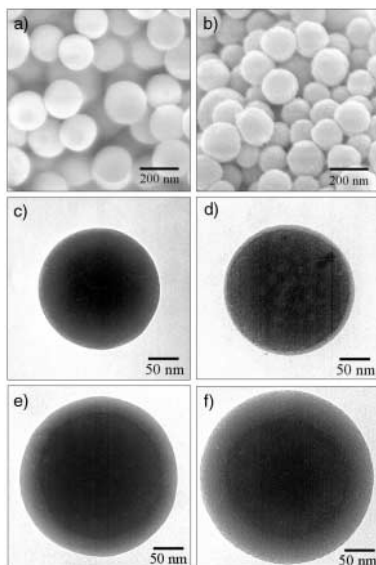
Advantages of Vapor Deposition Polymerization

- No Solvent (Environmental Friendly)
- No limitation on Monomers or Materials
- No limitation on surfaces (materials, morphology)
- Relatively Easy Process
- Good Processibility
- Conformal Coating

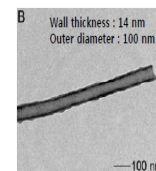
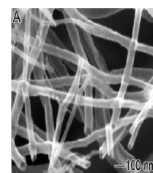
iCVD, oCVD, pyrolysis CVD, Vapor Deposition Polymerization

- K. Gleason (MIT)
- J. Lahann (Michigan)

Particle Coating



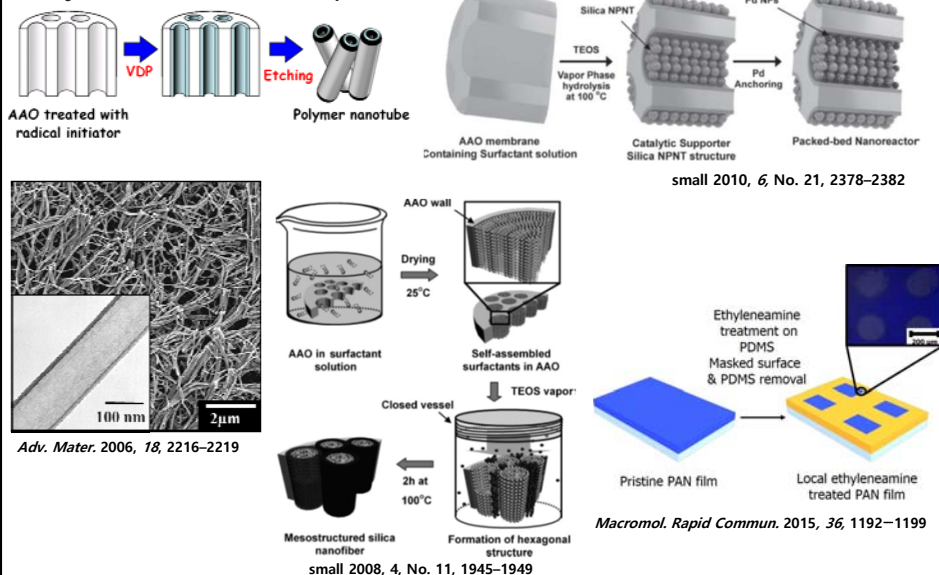
- Electrospin poly(styrene sulfonate) sodium nanofibers
- Vapor deposition polymerization of acrylonitrile
- Oxidative stabilization of poly(acrylonitrile) at 250 °C in air
- Removal of poly(styrene sulfonate) sodium core with water
- Carbonization at 900 °C under Ar flow



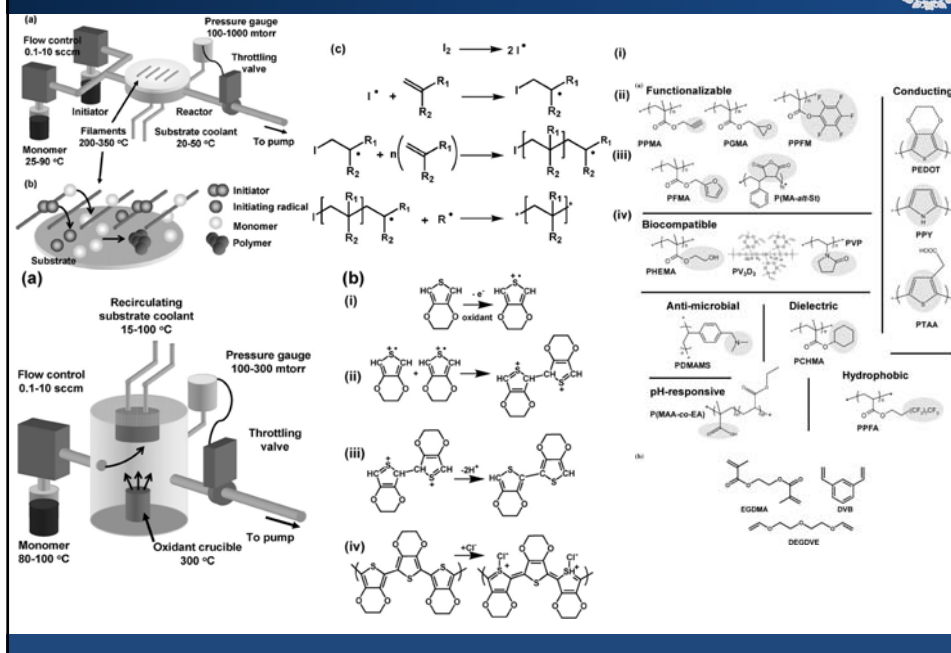
Once upon a time...

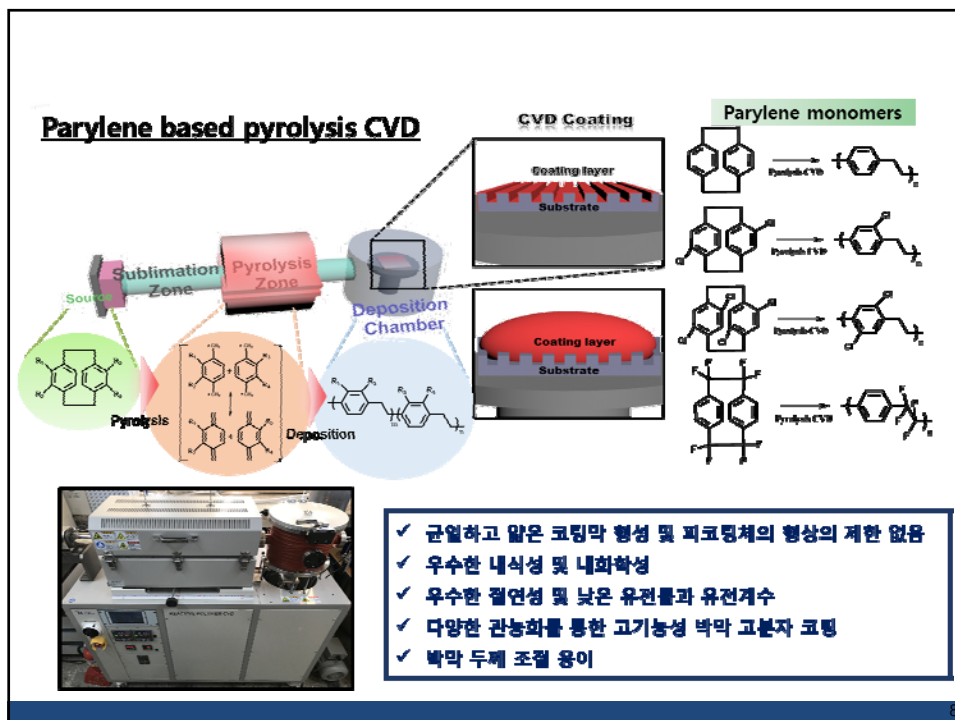
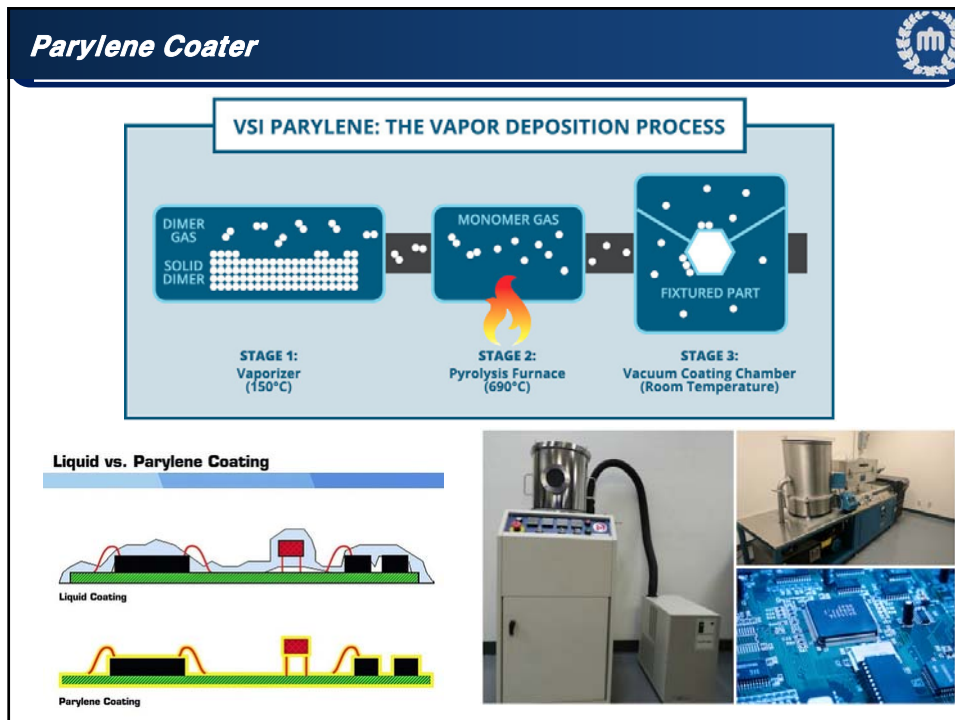


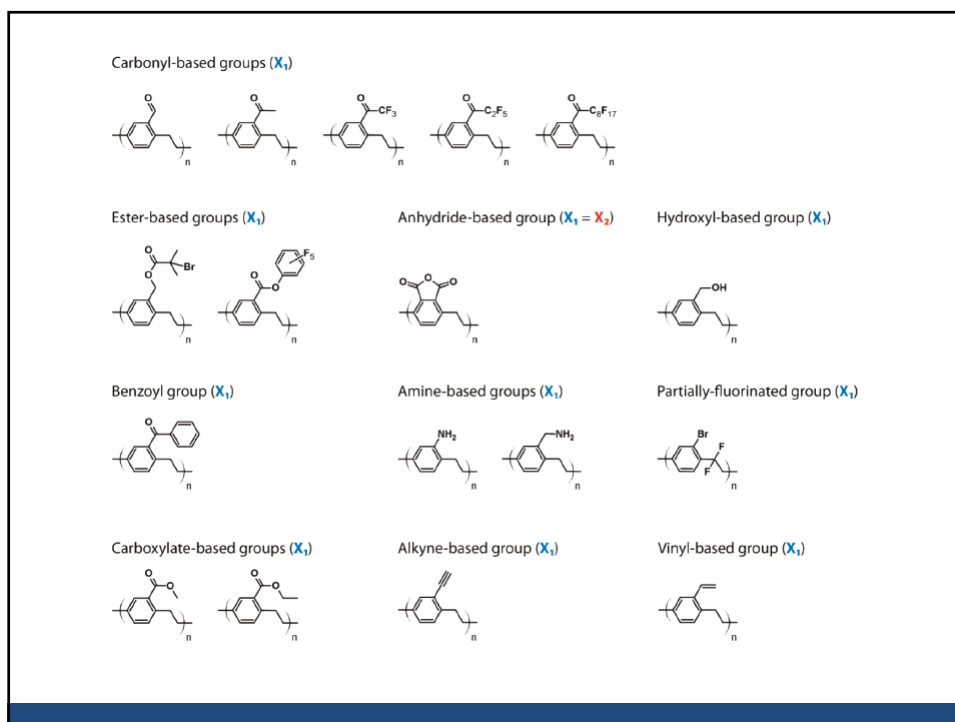
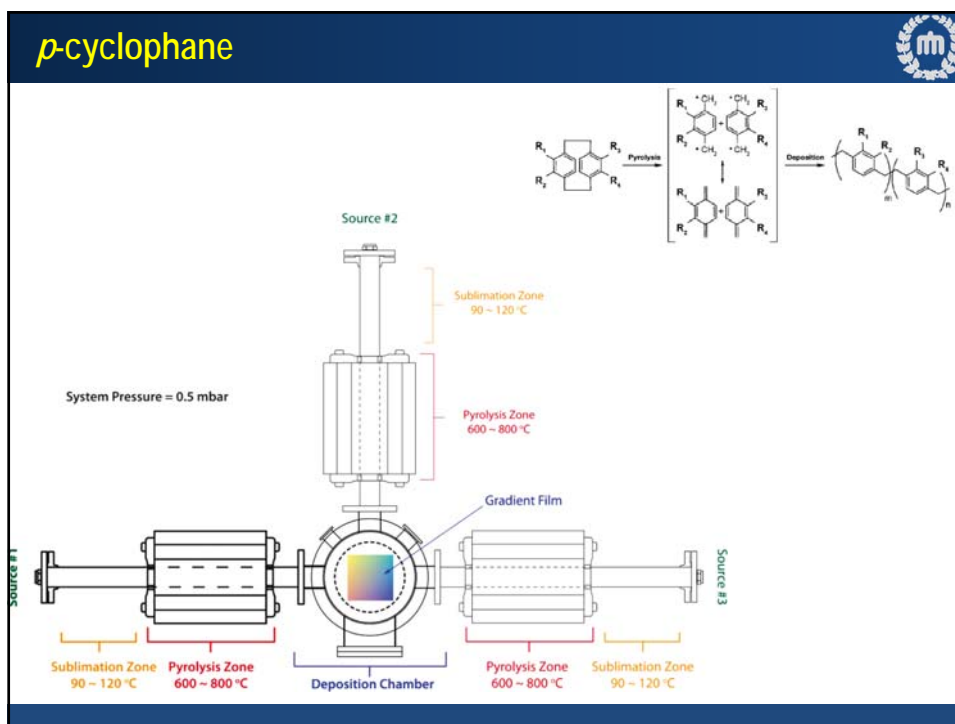
❖ My works about CVD in the past



iCVD/oCVD







REVIEW

Hall of Fame Article



www.advmaterinterfaces.de

Functionalization of Poly(*para*-xylylene)s—Opportunities and Challenges as Coating Material

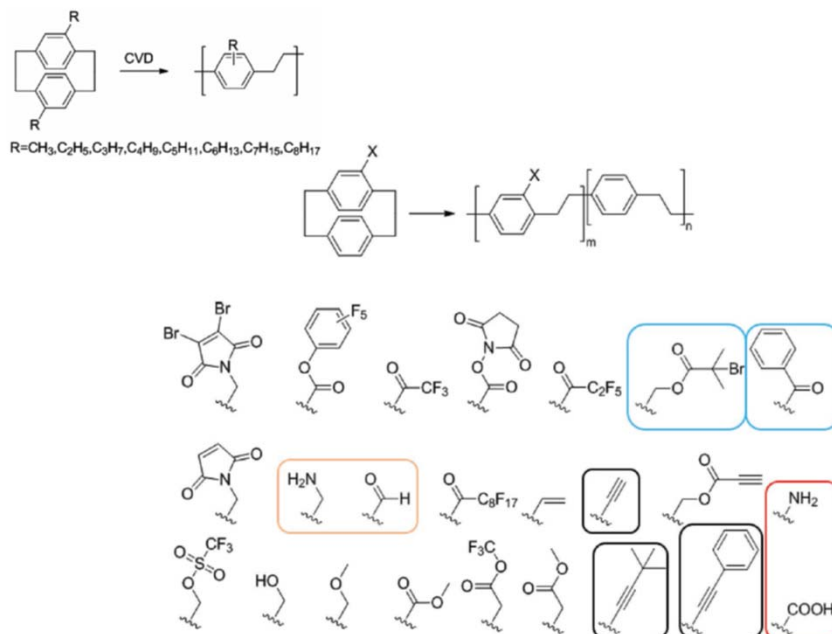
Tobias Moss and Andreas Greiner*

The chemical vapor deposition (CVD) of poly(*para*-xylylene)s (PPX) is an enabling technology for materials design as well as for numerous high-performance applications. Additionally, PPX possesses a unique set of structure–property relationships that can be tuned over a wide range. Different strategies vary from functionalization of the most used precursor [2,2] paracyclophane to the testing of new precursors and the copolymerization with various monomers. In this review, some recent developments on synthesis and properties of this unique class of polymers, the PPX, are reported.

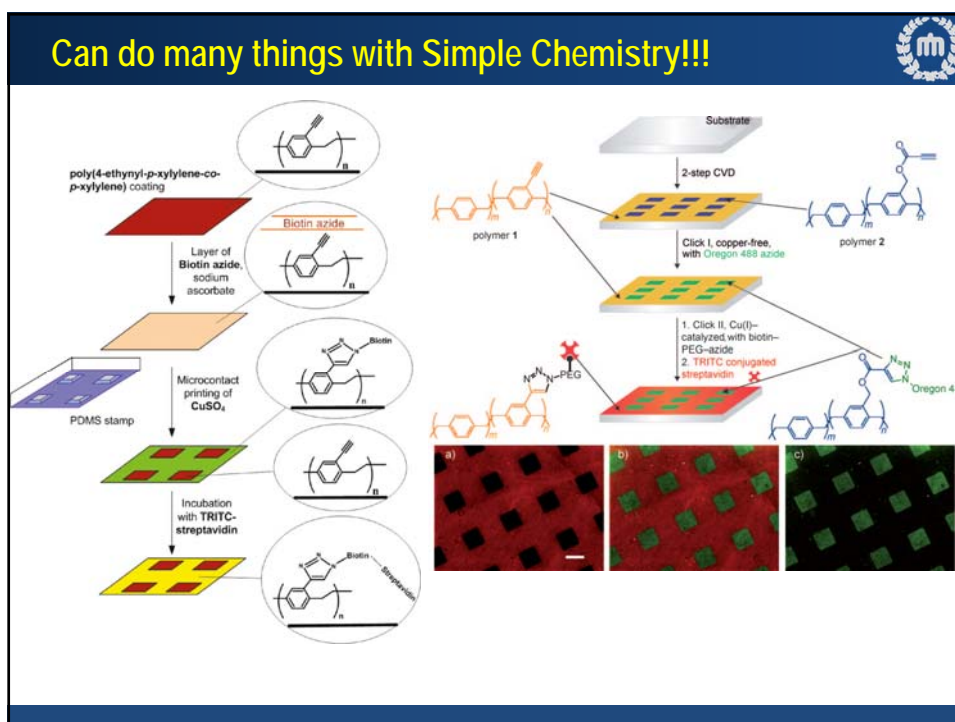
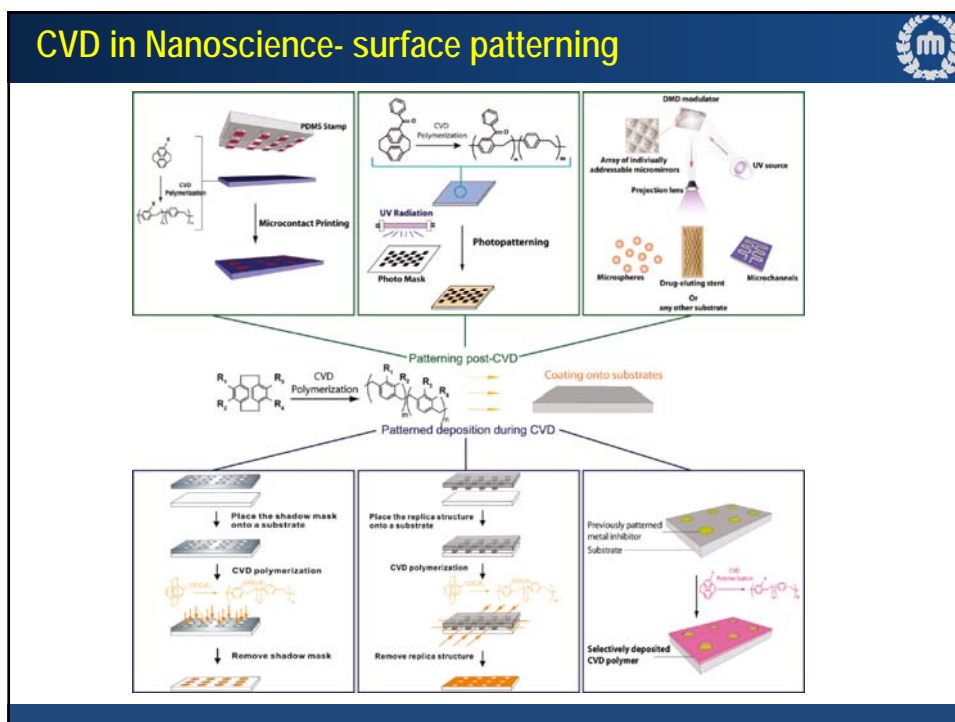
systems,^[14–16] organic light-emitting diodes,^[17] or in biological and medical applications.^[18–20] A relatively new area in the PPX research is the formation of reactive coatings. This can be achieved by the introduction of functional groups that are able to react in polymer analogous reactions.^[21–23]

This review should also provide an overview of the opportunities that especially functionalized PPXs made by CVD provide. First, some general remarks and examples of PPX made by CVD will be given before functionalized PPX will be

Adv. Mater. Interfaces **2020**, *7*, 1901858

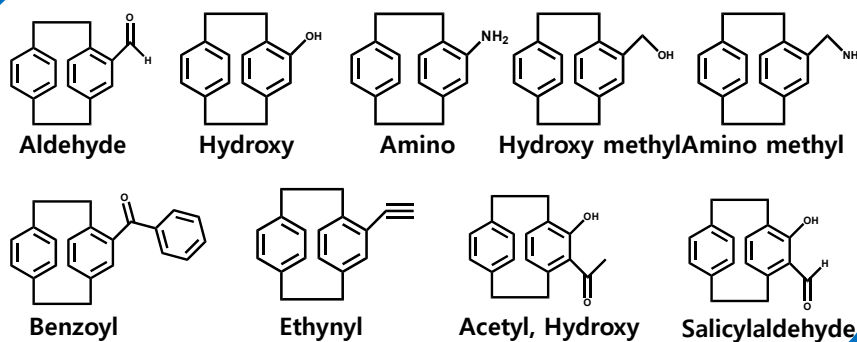
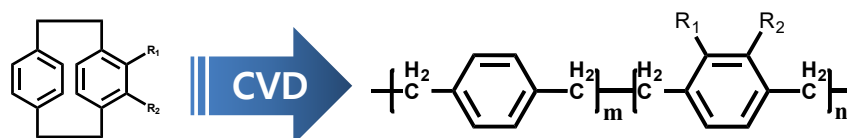


Adv. Mater. Interfaces **2020**, *7*, 1901858

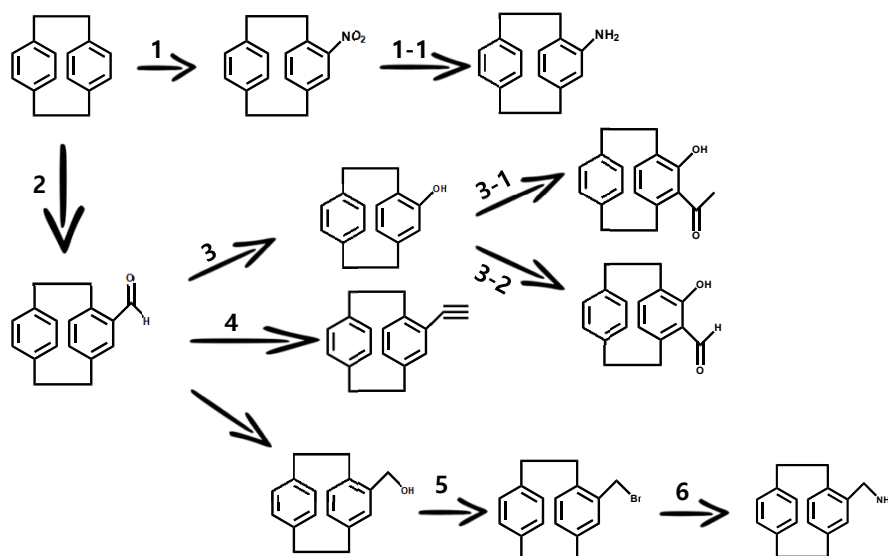


Currently Available Monomers in our Lab

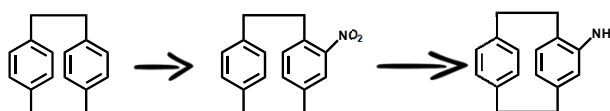
Monomer Library



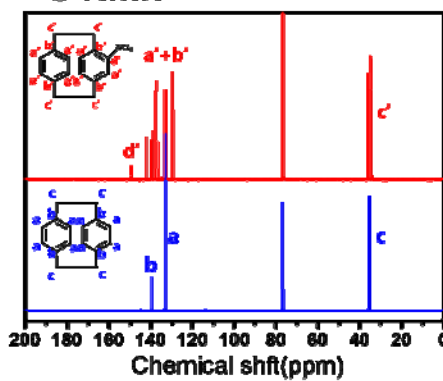
Functionalized Parylene



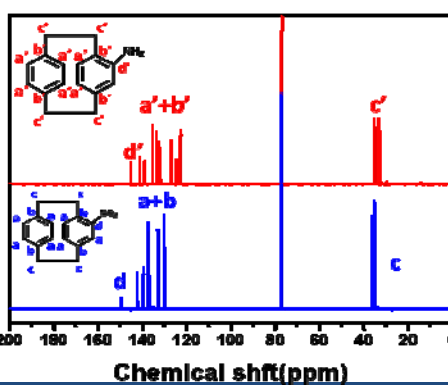
Amine



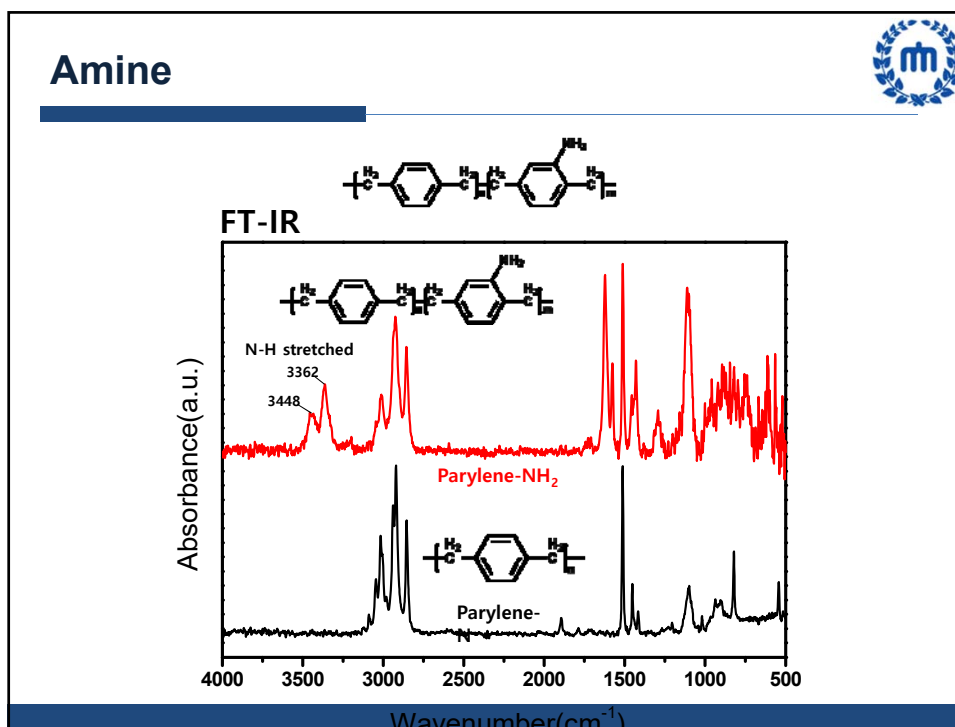
¹³C-NMR



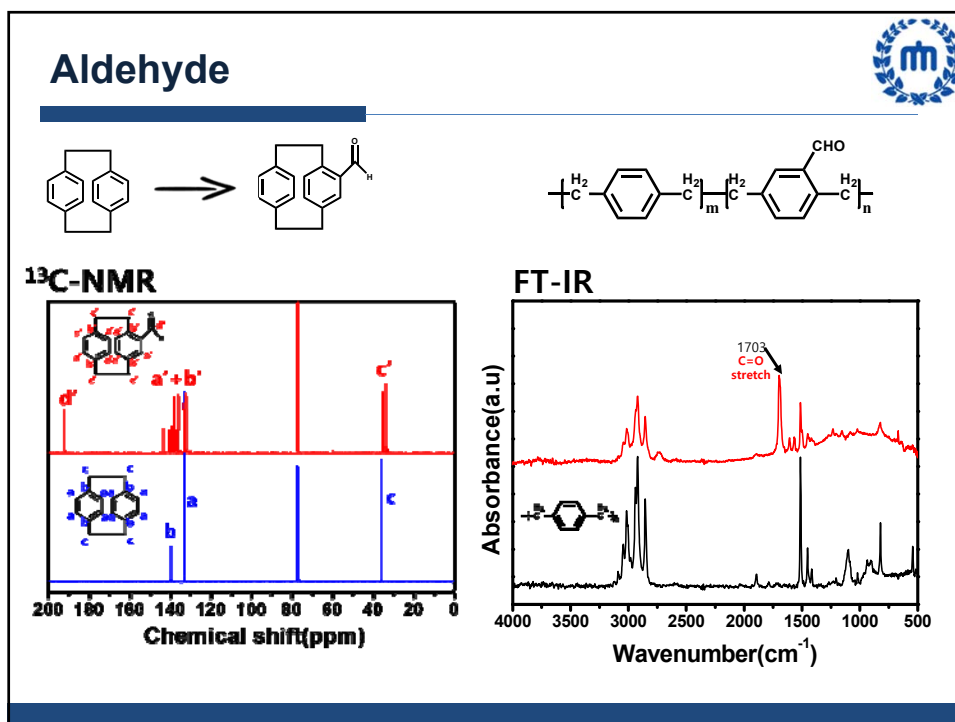
¹³C-NMR



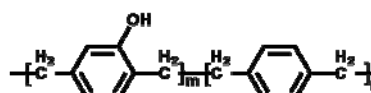
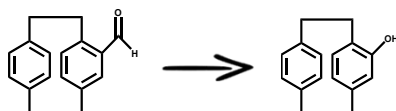
Amine



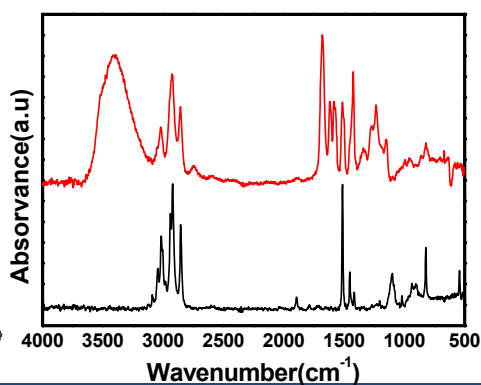
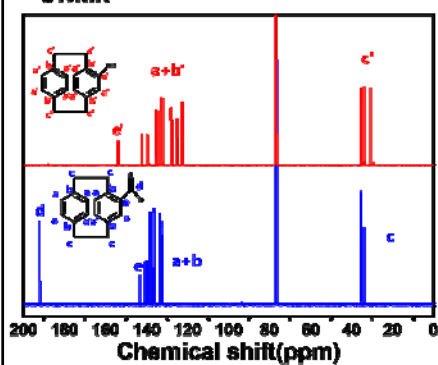
Aldehyde



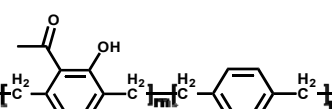
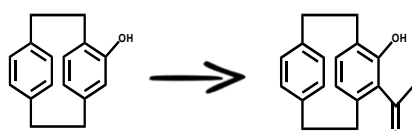
Hydroxyl



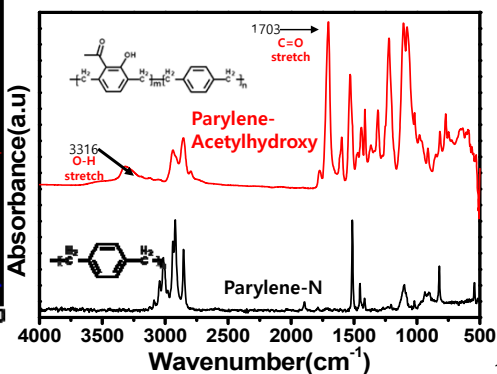
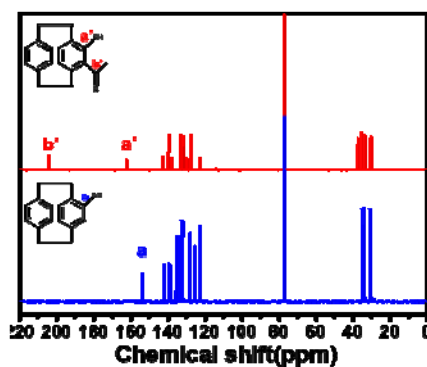
¹³C NMR



Dual (OH, Ketone)

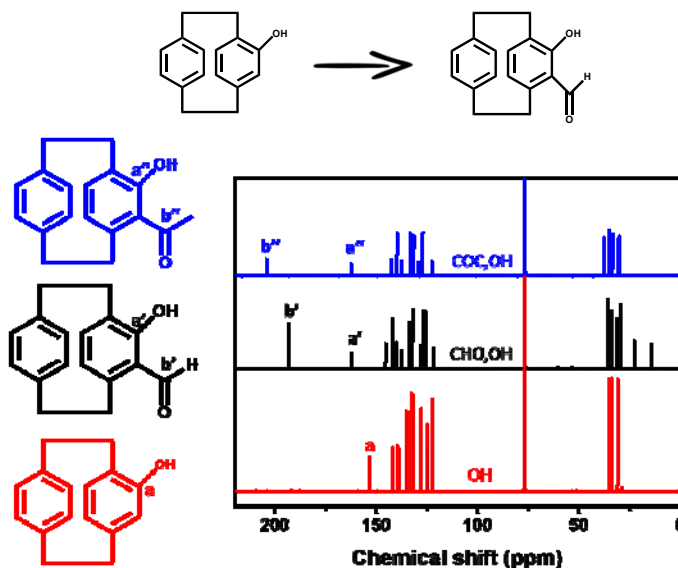


FT-IR

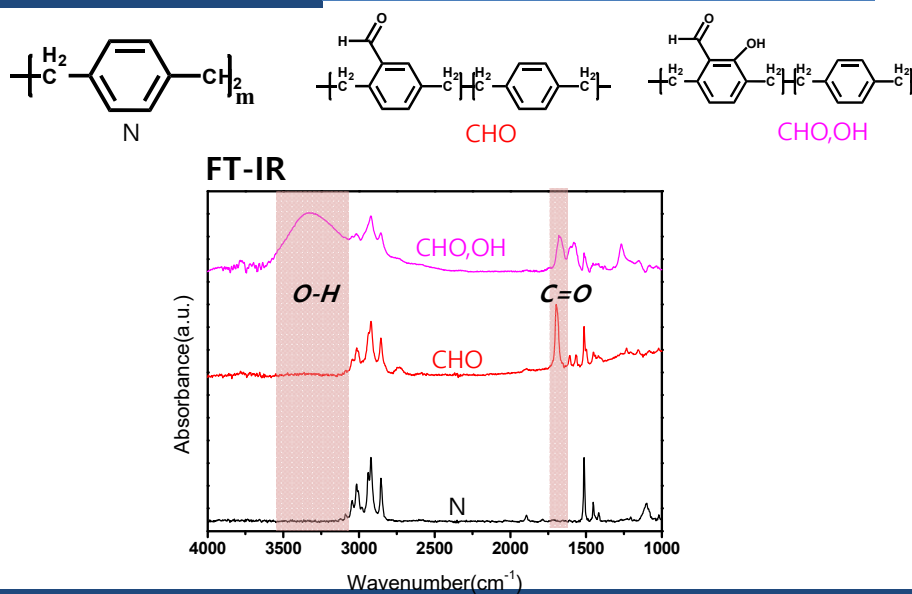


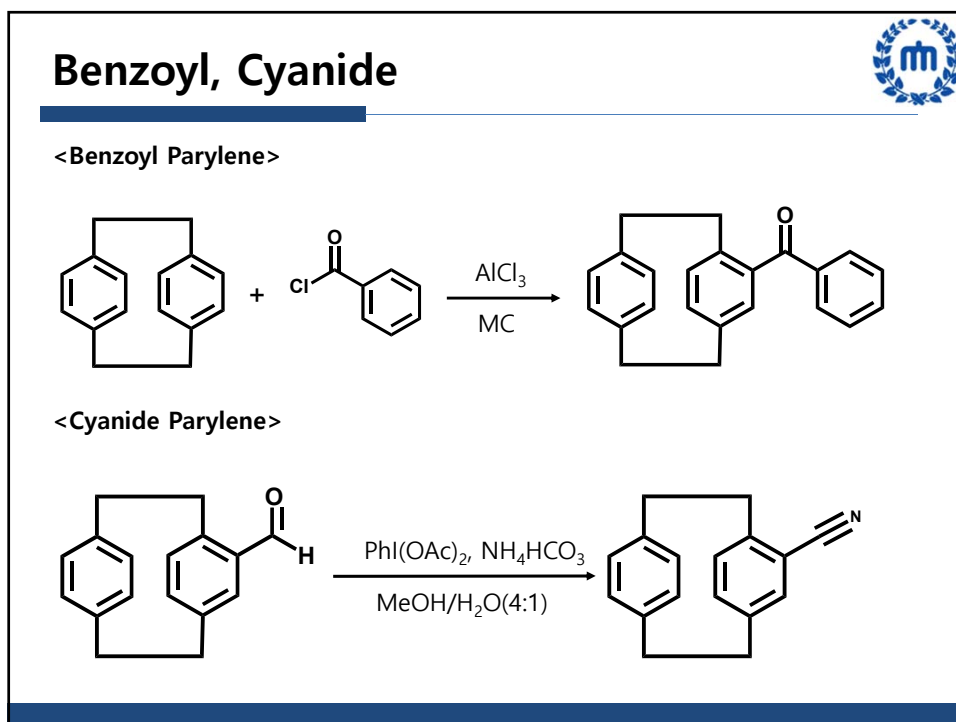
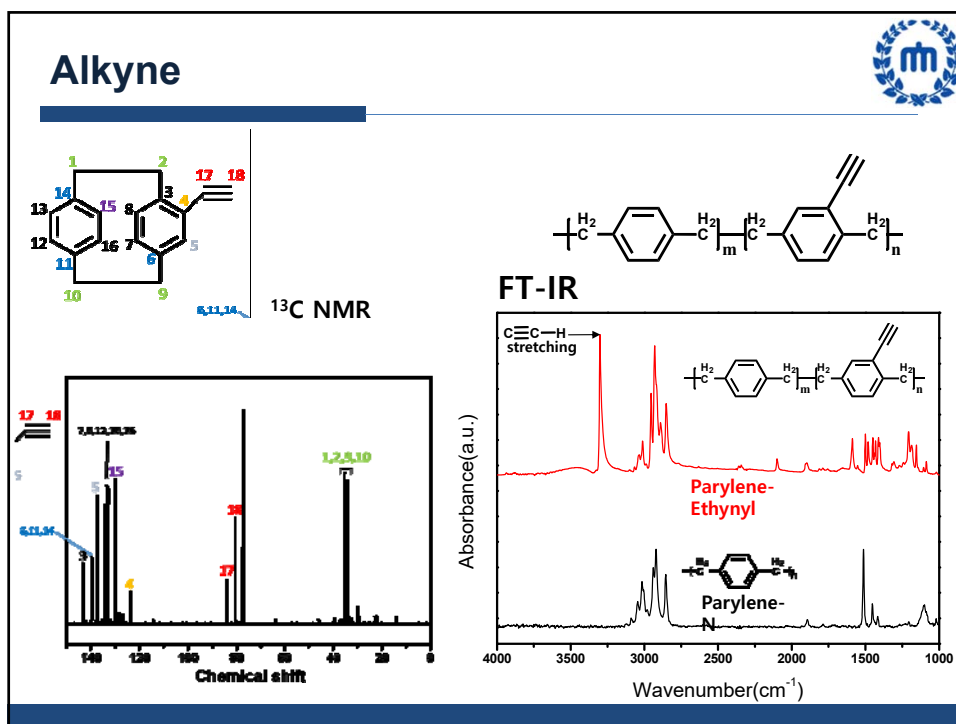
16

Dual (Salicyl Aldehyde)



Dual (Salicyl Aldehyde)

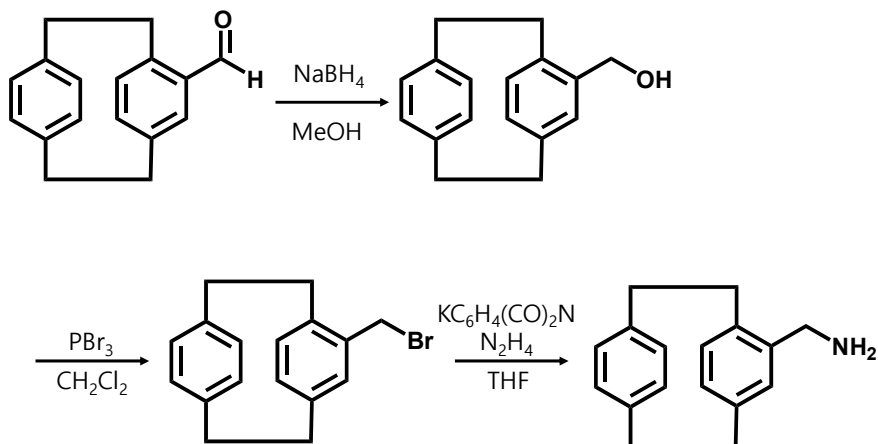




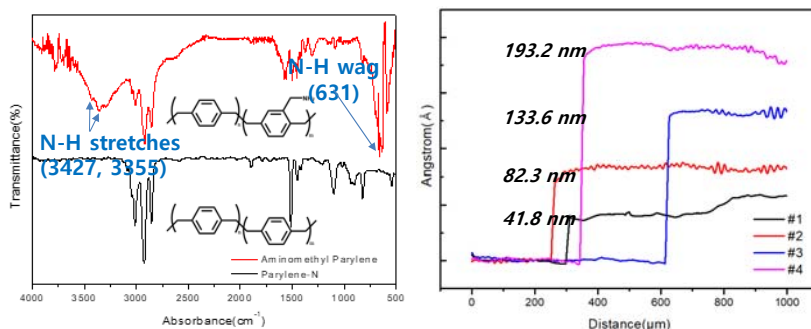
Methyl amino, Methyl hydroxyl



<Aminomethyl Parylene>



Aminomethyl Parylene

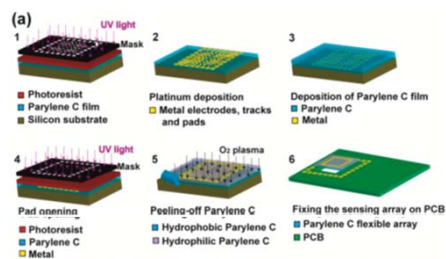


Gate dielectric Layer

Parylene works in Electronics



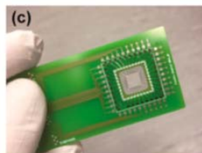
Majors are Encapsulation layer, Protection, and some of Dielectric layers in electronics!



Liquid Coating

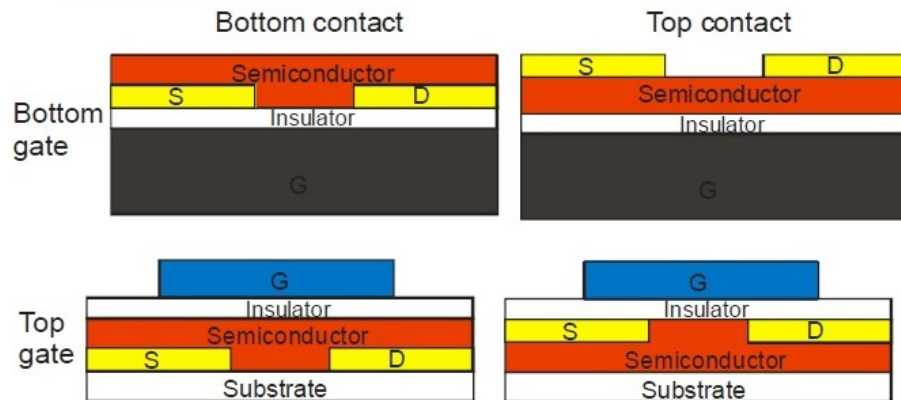
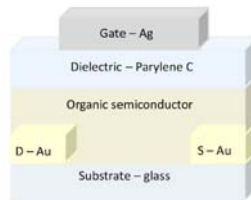


Parylene Coating



**PROTECTING
ELECTRONICS
WITH PARYLENE**

Basic of Basic for Thin Film Field Effect Transistor



Issues in Dielectric layers?



- ✓ *Low operation voltage*
- ✓ *High capacitance with Perfect Thin Film*

- ✓ *Low leakage current*
- ✓ *Stability*
- ✓ *Reliability*
- ✓ *Flexibility*

- *Chemical Composition*
- *Molecular Design*

- *Film Properties*
- *Processing Optimization*

Parameters

- *Monomer structure*
- *Molecular weight and MW distribution*
- *Density of film (number of pinhole)*
- *No Chemical reaction with organic semiconductors*

Previous works with Parylene as dielectric layer

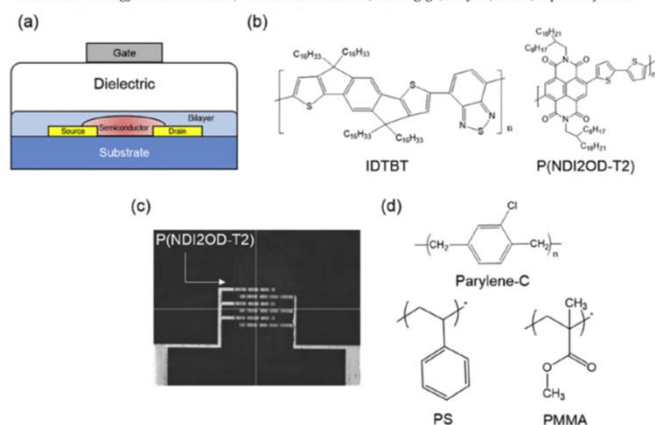


Parylene based bilayer flexible gate dielectric layer for top-gated organic field-effect transistors

Eul-Yong Shin^a, Eun-Young Choi^{b, **}, Yong-Young Noh^{a, *}

^a Department of Energy Materials Engineering, Dongguk University, 30, Pildong-ro 1-gil, Jung-gu, Seoul, 04620, Republic of Korea

^b Korea Atomic Energy Research Institute, Daedeok-daero 989-111, Yuseong-gu, Daejeon, 34057, Republic of Korea



Organic Electronics
46 (2017) 14–21

Previous works with CVD polymer films in Dielectric



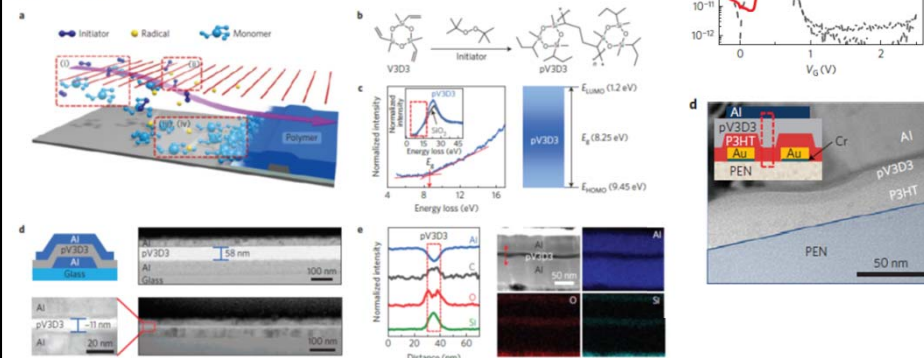
ARTICLES

PUBLISHED ONLINE 9 MARCH 2015 | DOI: 10.1038/NMAT4237

nature
materials

Synthesis of ultrathin polymer insulating layers by initiated chemical vapour deposition for low-power soft electronics

Hanul Moon^{1,2†}, Hyejeong Seong^{2,3†}, Woo Cheol Shin^{1,2†}, Won-Tae Park⁴, Mincheol Kim^{1,2}, Seungwon Lee^{1,2}, Jae Hoon Bong^{1,2}, Yong-Young Noh¹, Byung Jin Cho^{1,2*}, Seunghyup Yoo^{1,2*} and Sung Gap Im^{2,3*}



628 NATURE MATERIALS | VOL 14 | JUNE 2015



In addition to High dielectric constant, high capacitance, low leakage current, operation stability...etc

→ **Interfacial Optimization with f- Parylene**
 → **Obtaining InGaZnO (CVD based) semiconductor devices with Top or Bottom gate from**

Cowork with Prof. Kim H



CNU 충남대학교
CHUNGNAM NATIONAL UNIVERSITY

2018

101. Hyeon-Do Kim, Jong Heon Kim, Kyung Park, Joseph Park*, and **Hyun-Suk Kim***, "Corresponding author, "Highly Stable Thin-Film Transistors based on Indium Oxynitride Semiconductor" (In preparation).

100. Jong Heon Kim, Kyung Park, Su-Hi Choi, Yun Chang Park, Jung Hyun Kim, Chunjoong Kim, Si-Oso Kim, Joseph Park, and **Hyun-Suk Kim***, "Corresponding author "Effect of annealing temperature on the interfacial interaction of $\text{LiNi}_{0.5}\text{Mn}_{1.5}\text{O}_4$ thin film cathode with stainless-steel substrate", *Thin Solid Films* (Under review).

99. Dae Soo Park, Won Seok Choi, Hyunsil Kang, Seung-Wook Bae, **Hyun-Suk Kim**, Abdul K. Azad, Jun-Young Park, Jung Hyun Kim*, "X-ray Photoelectron Spectroscopic Study of Impregnated $\text{La}_{0.4}\text{Sr}_{0.6}\text{Ti}_{0.4}\text{Mn}_{0.6}\text{O}_{3-x}$ Anode Material for High Temperature-Operating Solid Oxide Fuel Cell", *Ceramics International* (Under review).

98. Kyung Park, Jong Heon Kim, Hyun-Woo Park, Ju-Hyeok Baek, Jonguk Bae, Kwon-Shik Park, Inbyeong Kang, Kiwon-Bum Chung, **Hyun-Suk Kim***, and Jang-Yeon Kwon*, "Corresponding author, "Highly Reliable Amorphous In-Ga-Zn-O Thin Film Transistors Through the Addition of Nitrogen Doping", *IEEE Transactions on Electron Devices* (Under review).

97. Ha-Hyun Nahm, Kanghoon Yim, **Hyun-Suk Kim**, and Seungyeu Han, "Electron Effective Mass Increased by Interstitial Impurities in Zinc Nitride: A Band-Gap Uncertainty Theory", *Advanced Materials* (Under review).

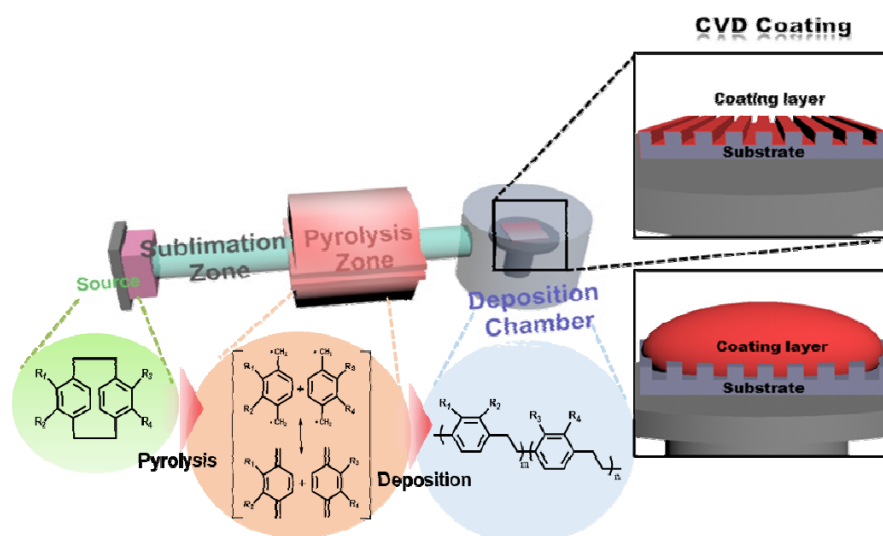
96. Jin Young Kim, Yu Kyoung Ryu, Javier Martinez, Marta Tello, Ramon V. Martinez, **Hyun-Suk Kim**, Yun Tang, Erio Tosatti, Ricardo Garcia, and Francesco Stellacci, "Nano "crystal radio" receivers as a femtoWatts tunable infrared room-temperature photodetectors", *Nature Materials* (Under review).

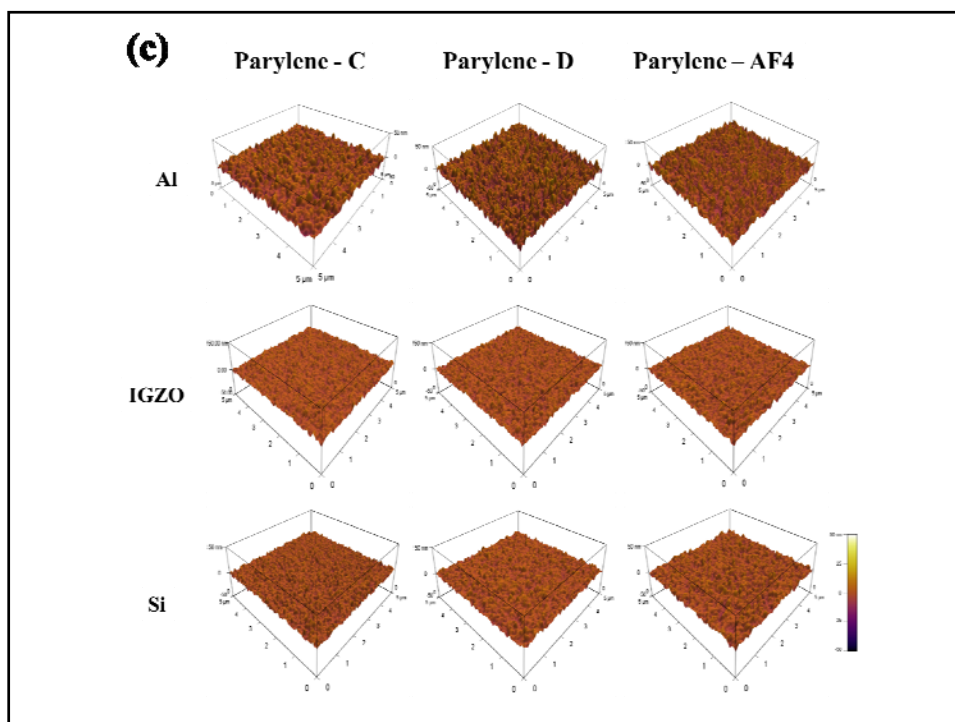
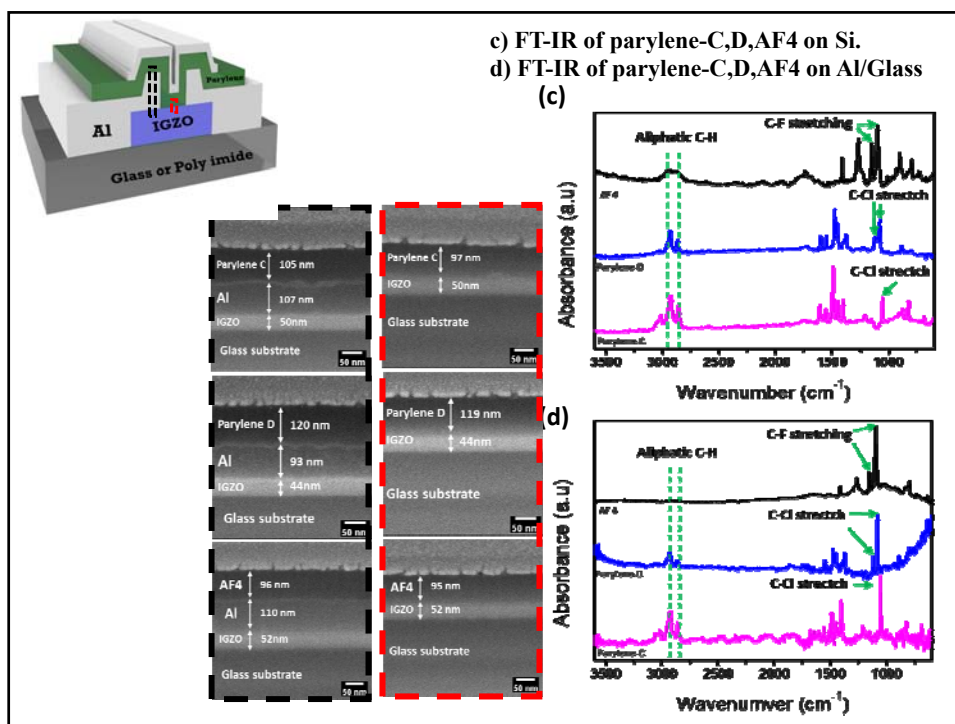
2017

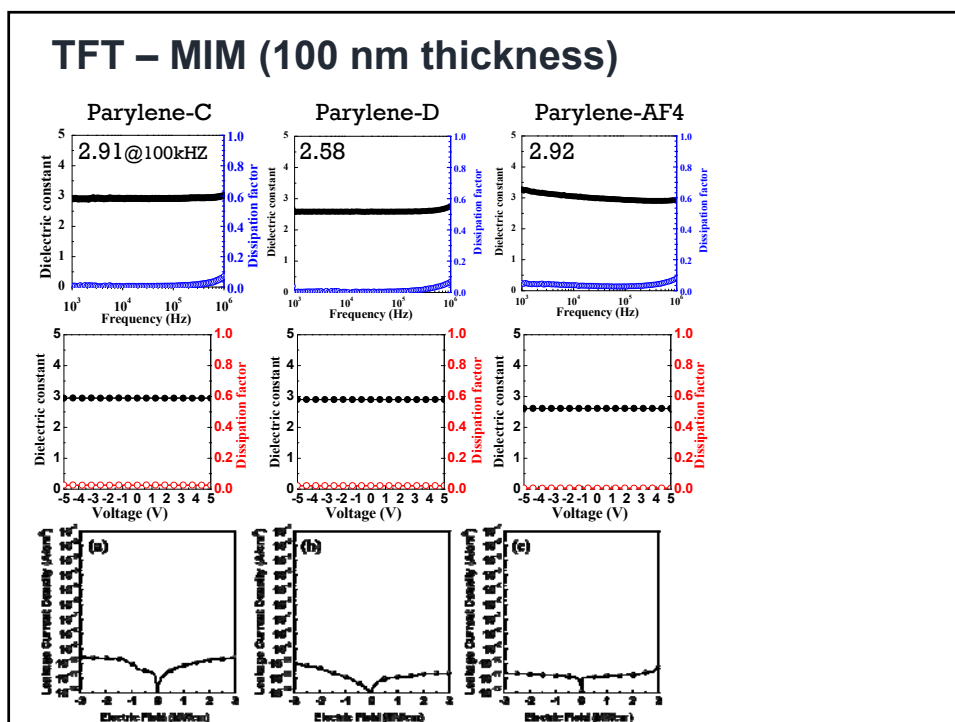
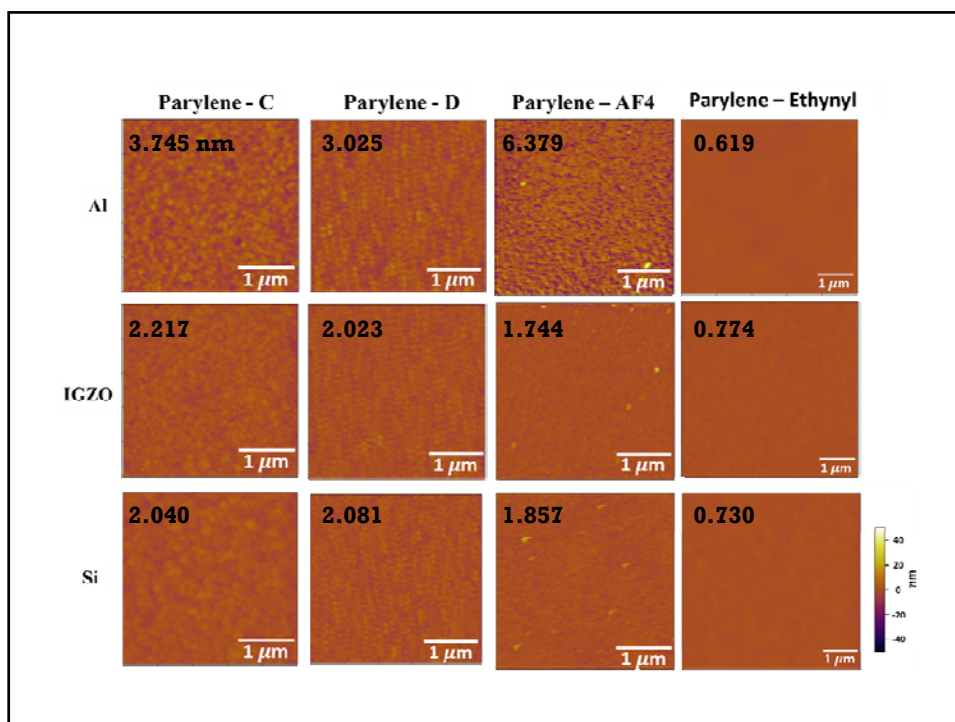
95. Jong Heon Kim, Hyeon-Do Kim, Dae-Gyu Yang, **Hyun-Suk Kim***, "Corresponding author, "High-Voltage $\text{LiNi}_{0.5}\text{Mn}_{1.5}\text{O}_4$ Thin Film Cathode Prepared by RF Sputtering", *ECS Transactions*, vol. 80 (Accepted).

94. Na Liu, Jongyool Baek, Seung Min Kim, Seongin Hong, Young Ki Hong, Yang Soo Kim, **Hyun-Suk Kim***, Sunkook Kim*, and Joseph Park*, "Corresponding author, "Stability Improvement of High-Performance Multilayer MoS_2 Field-Effect Transistors", *ACS Applied Materials & Interfaces*, vol. 9, 42943-42950 (2017) [JCR 10%] [IF = 7.504]

Schematic diagram of parylene coating with several monomer







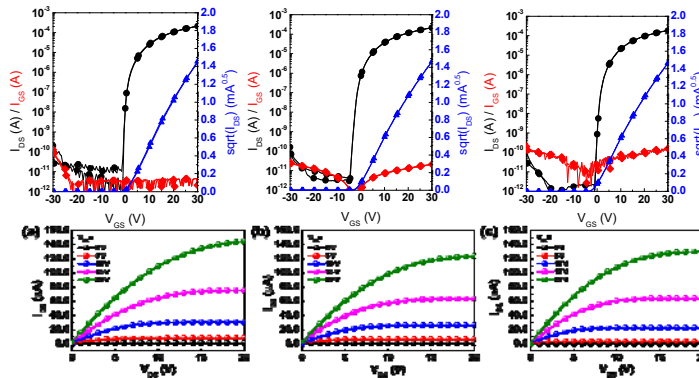
TFT - Transistor



Parylene-C

Parylene-D

Parylene-AF4

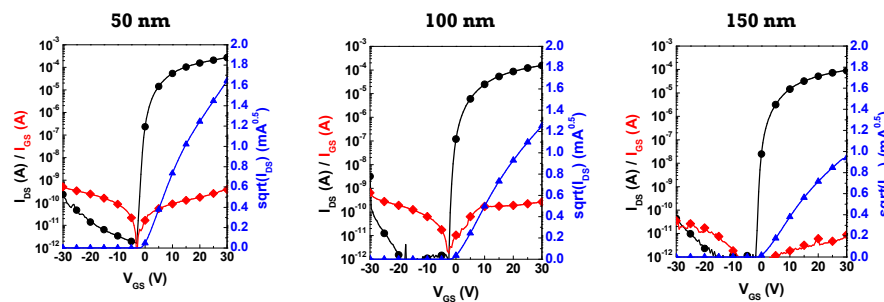


Gate dielectric	Thickness [nm]	Semiconductor	Mobility [cm ² /Vs]	V _{on} [V]	S.S [V/dec]	N _t [/cm ² eV]
SiO ₂	100	IGZO	2.39	-2.81	0.48	8.60 x 10 ¹¹
Parylene-C	100	IGZO	6.22	-0.52	0.21	4.11 x 10 ¹¹
Parylene-D	100	IGZO	5.81	-3.31	0.58	1.39 x 10 ¹²
Parylene-AF4	100	IGZO	6.23	0.02	0.41	9.42 x 10 ¹¹
Parylene-Ethynyl	74	IGZO	7.08	-3.72	0.20	6.02 x 10 ¹¹

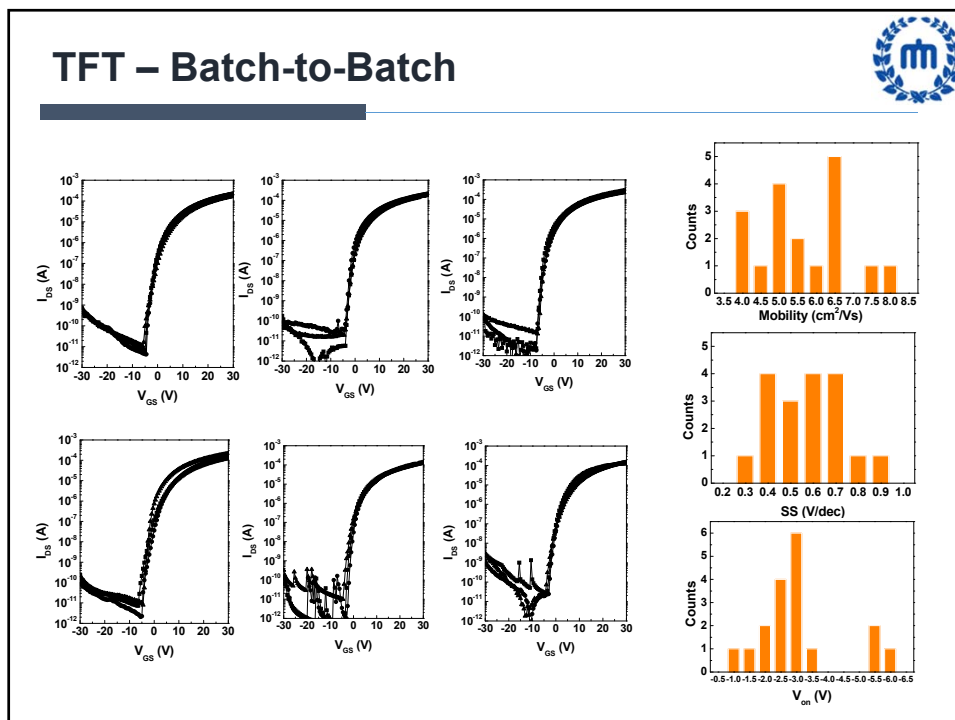
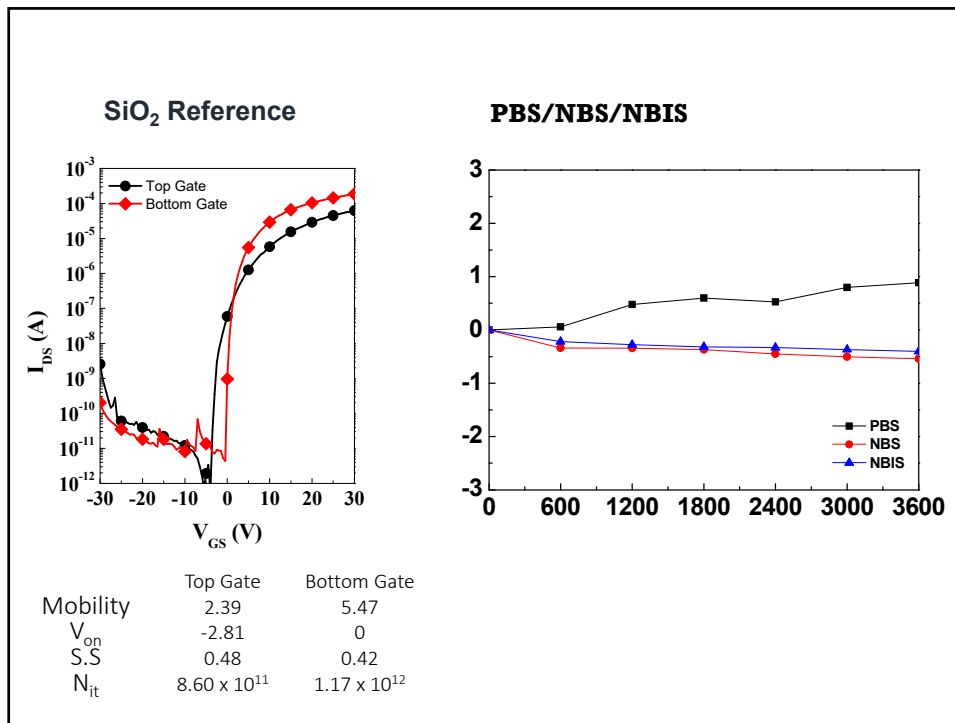
TFT - Transistor



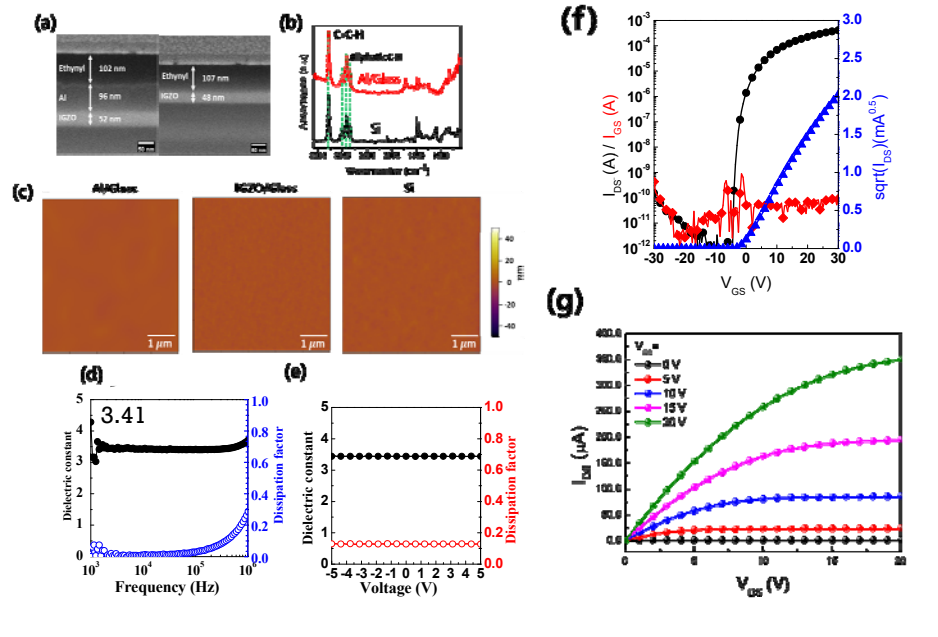
Parylene-AF4



Gate dielectric	Thickness [nm]	Semiconductor	Mobility [cm ² /Vs]	V _{on} [V]	S.S [V/dec]	N _t [/cm ² eV]
Parylene-AF4	50	IGZO	5.14	-1.69	0.46	2.15 x 10 ¹²
Parylene-AF4	100	IGZO	5.06	-1.62	0.41	9.42 x 10 ¹¹
Parylene-AF4	150	IGZO	4.83	-0.93	0.30	4.32 x 10 ¹¹



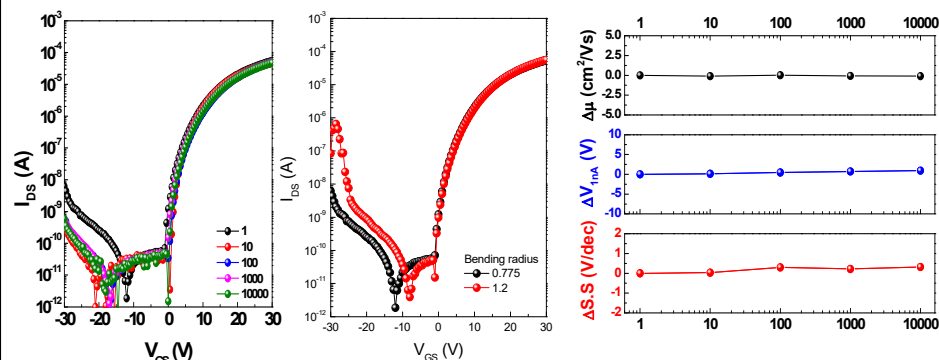
Parylene - ethynyl



TFT - Flexible

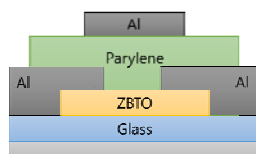


- Bending radius of 0.775 mm, calculated strain 0.68 %

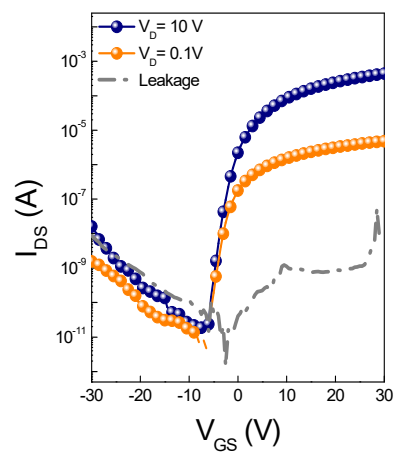
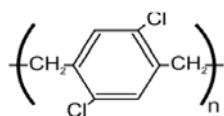


On-going Researches

TFT – High Mobility

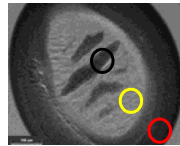


Gate dielectric
⇒ **Parylene D**



μ_{FE} (cm ² /Vs)	S.S (V/dec)	V_{TH} (V)	I_{on}/I_{off}
17.57	0.85	-1.79	$\sim 10^7$

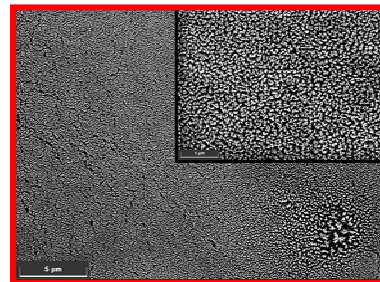
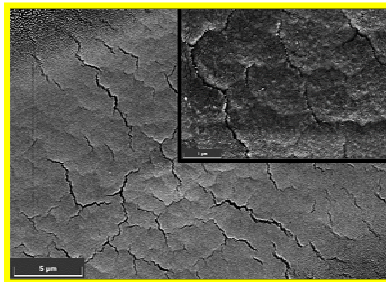
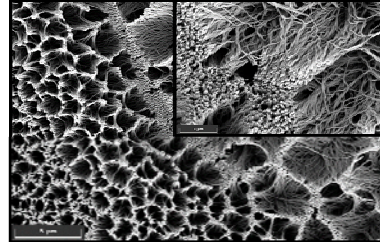
Nano Fiber



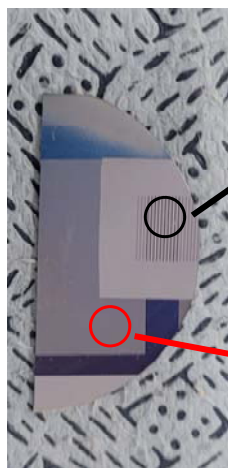
Si wafer

Parylene-N
Nano fiber

Liquid crystal

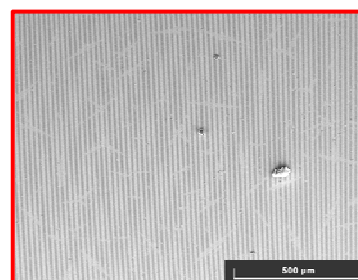
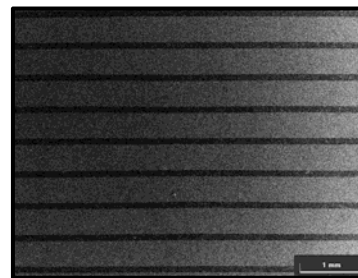


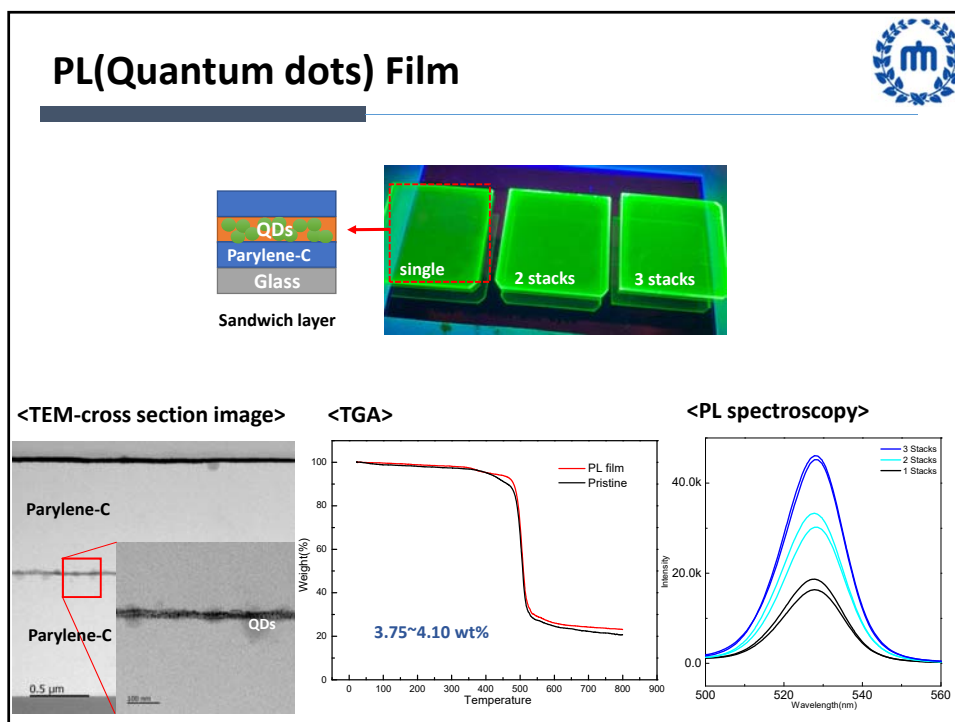
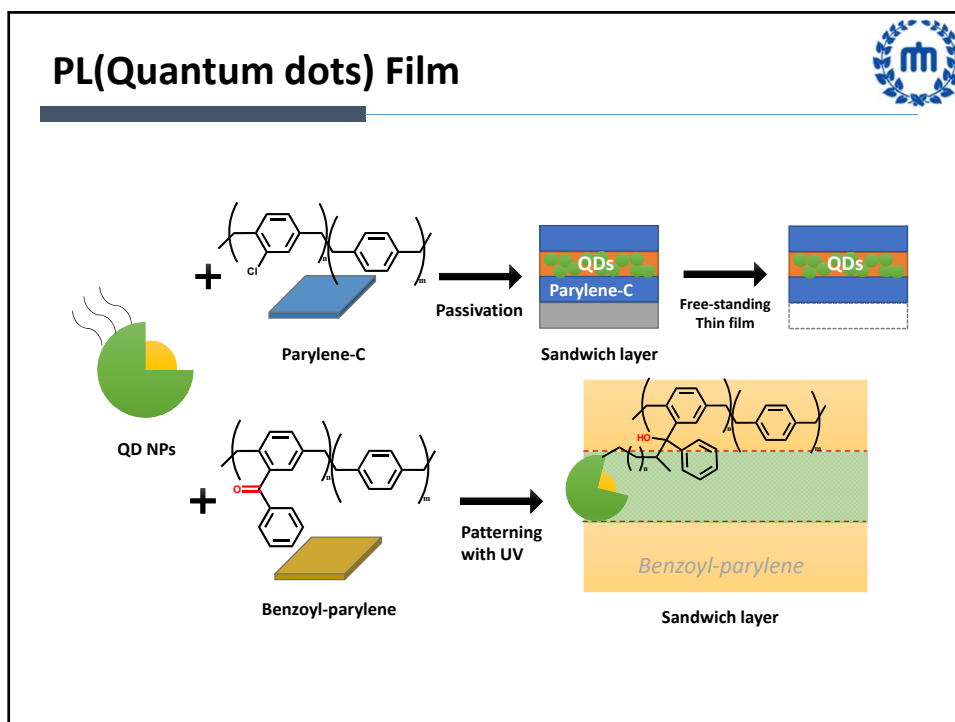
Photoreactive parylene



100 μm

10 μm





Liquid Material Encapped Parylene



Liquid electrolyte



Liquid Polymer(PEG)

연구개발 목표

